



DMN2230U

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

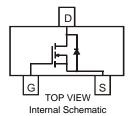
- Low On-Resistance
 - 110 m Ω @ $V_{GS} = 4.5V$
 - 145 m Ω @ $V_{GS} = 2.5V$
 - 230 m Ω @ $V_{GS} = 1.8V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 3 and 5)
- Qualified to AEC-Q101 Standards for High Reliability



SOT-23

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Units |
|-------------------------------|------------------|-------|-------|
| Drain-Source Voltage | V _{DSS} | 20 | V |
| Gate-Source Voltage | V _{GSS} | ±12 | V |
| Drain Current (Note 1) | I _D | 2.0 | А |
| Pulsed Drain Current (Note 4) | I _{DM} | 7 | А |

Thermal Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Units |
|---|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 1) | P_{D} | 600 | mW |
| Thermal Resistance, Junction to Ambient | $R_{	heta JA}$ | 208 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes:

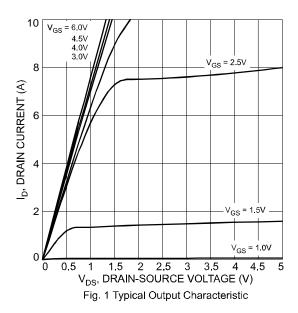
- 1. Device mounted on FR-4 PCB, or minimum recommended pad layout
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Repetitive rating, pulse width limited by junction temperature.
 Product manufactured with Green Molding Compound and does not contain Halogens or Sb₂O₃ Fire Retardants.

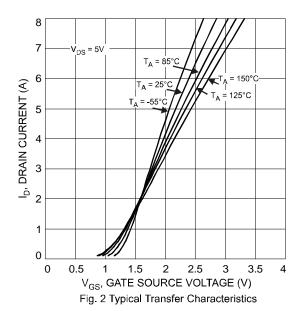


Electrical Characteristics @T_A = 25°C unless otherwise specified

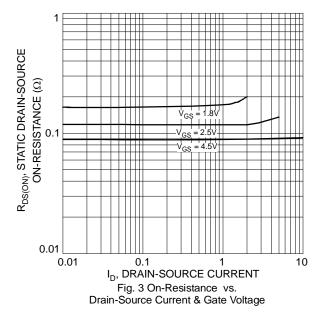
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|-----------------------------------|----------------------|-----|------------------|-----|------|---|--|
| OFF CHARACTERISTICS (Note 6) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | _ | _ | V | $V_{GS} = 0V, I_D = 10\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μА | V _{DS} = 20V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±10 | μА | $V_{GS} = \pm 12V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 6) | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.5 | _ | 1.0 | V | $V_{DS} = V_{CS}, I_D = 250 \mu A$ | |
| | R _{DS} (ON) | _ | 81 113 170 | 110 | | $V_{GS} = 4.5V, I_D = 2.5A$ | |
| Static Drain-Source On-Resistance | | | | 145 | mΩ | V _{GS} = 2.5V, I _D = 1.5A | |
| | | | | 230 | | V _{GS} = 1.8V, I _D = 1.0A | |
| Forward Transfer Admittance | Y _{fs} | _ | 5 | _ | S | V _{DS} =5V, I _D = 2.4A | |
| Diode Forward Voltage (Note 6) | V _{SD} | _ | 0.8 | 1.1 | V | V _{GS} = 0V, I _S = 1.05A | |
| DYNAMIC CHARACTERISTICS | • | | | | | | |
| Input Capacitance | C _{iss} | _ | 188 | _ | pF | | |
| Output Capacitance | Coss | _ | 44 | _ | pF | $V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | _ | 30 | _ | pF | 1 – 1.00112 | |
| Turn-On Delay Time | t _{d(on)} | _ | 8 | _ | | | |
| Rise Time | t _r | _ | 3.8 | _ | ns | $V_{DD} = 10V, R_L = 10\Omega$ | |
| Turn-Off Delay Time | t _{d(off)} | _ | 19.6 | _ | ns | $I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$ | |
| Fall Time | t _f | _ | 8.3 | | | | |

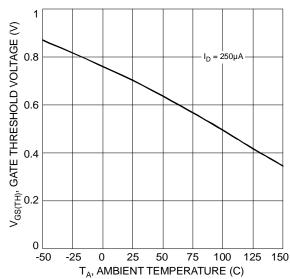
Notes: 6. Short duration pulse test used to minimize self-heating effect.

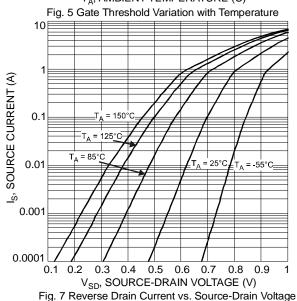












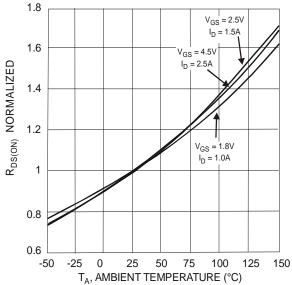
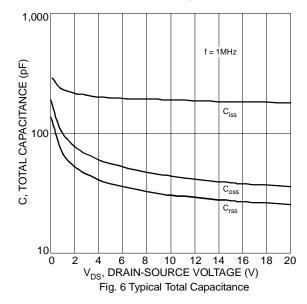


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



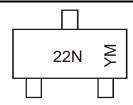


Ordering Information (Note 7)

| Part Number | Case | Packaging |
|-------------|--------|------------------|
| DMN2230U-7 | SOT-23 | 3000/Tape & Reel |

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

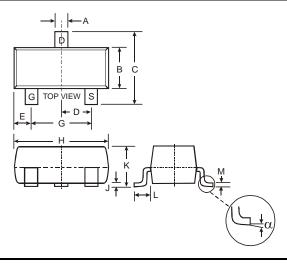


22N = Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key (If Applicable)

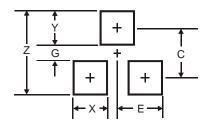
| Year | 20 | 07 | 20 | 08 | 20 | 09 | 20 | 10 | 20 | 11 | 20 | 12 |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | l | J | \ | / | V | V | > | < | ` | 1 | Z | 7 |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

Package Outline Dimensions



| SOT-23 | | | | | |
|---------|----------------------|-------|--|--|--|
| Dim | Min | Max | | | |
| Α | 0.37 | 0.51 | | | |
| В | 1.20 | 1.40 | | | |
| С | 2.30 | 2.50 | | | |
| D | 0.89 | 1.03 | | | |
| Е | 0.45 | 0.60 | | | |
| G | 1.78 | 2.05 | | | |
| Н | 2.80 | 3.00 | | | |
| J | 0.013 | 0.10 | | | |
| K | 0.903 | 1.10 | | | |
| L | 0.45 | 0.61 | | | |
| М | 0.085 | 0.180 | | | |
| α | 0° | 8° | | | |
| All Dir | All Dimensions in mm | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|------------------|
| Z | 3.4 |
| G | 0.7 |
| Х | 0.9 |
| Υ | 1.4 |
| С | 2.0 |
| E | 0.9 |

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